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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

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Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192К х 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f405vgt6v

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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Figure 4. Compatible board design between STM32F2 and STM32F40xxx for LQFP176 and BGA176 packages



	I	Pin r	numb	er							
LQFP64	06dSDJW	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
-	A8	-	143	C6	171	PDR_ON	Ι	FT	-	-	-
64	A1	10 0	144	C5	172	V _{DD}	s	-	-	-	-
-	-	-	-	D4	173	PI4	I/O	FT	-	TIM8_BKIN / DCMI_D5/ EVENTOUT	-
-	-	-	-	C4	174	PI5	I/O	FT	-	TIM8_CH1 / DCMI_VSYNC/ EVENTOUT	-
-	-	-	-	C3	175	PI6	I/O	FT	-	TIM8_CH2 / DCMI_D6/ EVENTOUT	-
-	-	-	-	C2	176	PI7	I/O	FT	-	TIM8_CH3 / DCMI_D7/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions (continued)

1. Function availability depends on the chosen device.

PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited:
 The speed should not exceed 2 MHz with a maximum load of 30 pF.

- These I/Os must not be used as a current source (e.g. to drive an LED).

3. Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F4xx reference manual, available from the STMicroelectronics website: www.st.com.

4. FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).

If the device is delivered in an UFBGA176 or WLCSP90 and the BYPASS_REG pin is set to VDD (Regulator off/internal reset ON mode), then PA0 is used as an internal Reset (active low). 5.

Pins ⁽¹⁾				WI CEROO		
	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND 16 bit	LQFP100 ⁽²⁾	(2)
PE2	-	A23	A23	-	Yes	-
PE3	-	A19	A19	-	Yes	-
PE4	-	A20	A20	-	Yes	-
PE5	-	A21	A21	-	Yes	-
PE6	-	A22	A22	-	Yes	-
PF0	A0	A0	-	-	-	-

Table 8. FSMC pin definition



Bus	Boundary address	Peripheral
	0x4004 0000 - 0x4007 FFFF	USB OTG HS
	0x4002 9400 - 0x4003 FFFF	Reserved
	0x4002 9000 - 0x4002 93FF	
	0x4002 8C00 - 0x4002 8FFF	
	0x4002 8800 - 0x4002 8BFF	ETHERNET MAC
	0x4002 8400 - 0x4002 87FF	
	0x4002 8000 - 0x4002 83FF	
	0x4002 6800 - 0x4002 7FFF	Reserved
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0x4002 5000 - 0x4002 5FFF	Reserved
	0x4002 4000 - 0x4002 4FFF	BKPSRAM
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
ALIDI	0x4002 3800 - 0x4002 3BFF	RCC
	0x4002 3400 - 0x4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
	0x4002 2400 - 0x4002 2FFF	Reserved
	0x4002 2000 - 0x4002 23FF	GPIOI
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1800 - 0x4002 1BFF	GPIOG
	0x4002 1400 - 0x4002 17FF	GPIOF
	0x4002 1000 - 0x4002 13FF	GPIOE
	0x4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA
	0x4001 5800- 0x4001 FFFF	Reserved

Table 10. register boundary addresses (continued)



5.1.7 Current consumption measurement



Figure 22. Current consumption measurement scheme

5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 11: Voltage characteristics*, *Table 12: Current characteristics*, and *Table 13: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard, extended mission profiles are available on demand.

Symbol	Ratings	Min	Мах	Unit
$V_{DD}-V_{SS}$	External main supply voltage (including V_{DDA} , V_{DD}) ⁽¹⁾	-0.3	4.0	
V	Input voltage on five-volt tolerant pin ⁽²⁾	V _{SS} -0.3	V _{DD} +4	V
♥ IN	Input voltage on any other pin	V _{SS} -0.3	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	
$ V_{SSX} - V_{SS} $	Variations between all the different ground pins including V_{REF^-}	-	50	mV
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 5.3.14: Absolute maximum ratings (electrical sensitivity)		

Table 11. Voltage characteristics

 All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum value must always be respected. Refer to *Table 12* for the values of the maximum allowed injected current.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
M	Brownout level 2	Falling edge	2.44	2.50	2.56	V
VBOR2	threshold	Rising edge	2.53	2.59	2.63	V
M	Brownout level 3	Falling edge	2.75	2.83	2.88	V
V BOR3	threshold	Rising edge	2.85	2.92	2.97	V
V _{BORhyst} ⁽¹⁾	BOR hysteresis	-	-	100	-	mV
T _{RSTTEMPO} ⁽¹⁾⁽²⁾	Reset temporization	-	0.5	1.5	3.0	ms
I _{RUSH} ⁽¹⁾	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
E _{RUSH} ⁽¹⁾	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	V _{DD} = 1.8 V, T _A = 105 °C, I _{RUSH} = 171 mA for 31 μs	-	-	5.4	μC

 Table 19. Embedded reset and power control block characteristics (continued)

1. Guaranteed by design.

2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

5.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 22: Current consumption measurement scheme*.

All Run mode current consumption measurements given in this section are performed using a CoreMark-compliant code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are configured as analog inputs by firmware.
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted to f_{HCLK} frequency (0 wait state from 0 to 30 MHz, 1 wait state from 30 to 60 MHz, 2 wait states from 60 to 90 MHz, 3 wait states from 90 to 120 MHz, 4 wait states from 120 to 150 MHz, and 5 wait states from 150 to 168 MHz).
- When the peripherals are enabled HCLK is the system clock, f_{PCLK1} = f_{HCLK}/4, and f_{PCLK2} = f_{HCLK}/2, except is explicitly mentioned.
- The maximum values are obtained for V_{DD} = 3.6 V and maximum ambient temperature (T_A), and the typical values for T_A= 25 °C and V_{DD} = 3.3 V unless otherwise specified.



Symbol				Тур		Ма		
	Parameter	rameter Conditions		a = 25 °	C	T _A = 85 °C	T _A = 105 °C	Unit
			V _{BAT} = 1.8 V	V _{BAT} = 2.4 V	V _{BAT} = 3.3 V	V _{BAT} =	= 3.6 V	
I _{DD_VBA} T	Pookup	Backup SRAM ON, low-speed oscillator and RTC ON	1.29	1.42	1.68	6	11	
	domain supply	Backup SRAM OFF, low-speed oscillator and RTC ON	0.62	0.73	0.96	3	5	μA
	current	Backup SRAM ON, RTC OFF	0.79	0.81	0.86	5	10	
		Backup SRAM OFF, RTC OFF	0.10	0.10	0.10	2	4	

Table 25.	Typical and	maximum	current	consumptio	ns in	VBAT	mode

1. Guaranteed by characterization.







Figure 29. Typical V_{BAT} current consumption (LSE and RTC ON/backup RAM ON)



floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 28: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

 I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

 V_{DD} is the MCU supply voltage

 $f_{\mbox{SW}}$ is the I/O switching frequency

C is the total capacitance seen by the I/O pin: C = C_{INT} + C_{EXT}

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.





Figure 33. Typical application with a 32.768 kHz crystal

5.3.9 Internal clock source characteristics

The parameters given in *Table 34* and *Table 35* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

High-speed internal (HSI) RC oscillator

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI}	Frequency	-	-	16	-	MHz
	HSI user trimming step ⁽²⁾	-	-	-	1	%
		$T_A = -40$ to 105 °C ⁽³⁾	-8	-	4.5	%
ACCHSI	Accuracy of the HSI oscillator	$T_A = -10$ to 85 °C ⁽³⁾	-4	-	4	%
		$T_A = 25 \ ^{\circ}C^{(4)}$	-1	-	1	%
t _{su(HSI)} ⁽²⁾	HSI oscillator startup time	-	-	2.2	4	μs
I _{DD(HSI)} ⁽²⁾	HSI oscillator power consumption	-	-	60	80	μA

Table 34. HSI oscillator characteristics ⁽¹⁾

1. V_{DD} = 3.3 V, T_A = -40 to 105 °C unless otherwise specified.

2. Guaranteed by design.

3. Guaranteed by characterization.

4. Factory calibrated, parts not soldered.

Low-speed internal (LSI) RC oscillator

Table 35.	LSI	oscillator	characteristics	(1)
-----------	-----	------------	-----------------	-----

Symbol	Parameter	Min	Тур	Мах	Unit
f _{LSI} ⁽²⁾	Frequency	17	32	47	kHz
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	15	40	μs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	0.4	0.6	μA

1. V_{DD} = 3 V, T_A = -40 to 105 °C unless otherwise specified.

2. Guaranteed by characterization.

3. Guaranteed by design.



Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table	46	Electrical	sensitivities
Table	τυ.	LICCUICAI	30113111411103

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105 \text{ °C conforming to JESD78A}$	II level A

5.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of 5 μ A/+0 μ A range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in Table 47.



5.3.23 V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Тур	Мах	Unit
R	Resistor bridge for V _{BAT}	-	50	-	KΩ
Q	Ratio on V _{BAT} measurement	-	2	-	
Er ⁽¹⁾	Error on Q	-1	-	+1	%
T _{S_vbat} ⁽²⁾⁽²⁾	ADC sampling time when reading the V _{BAT} 1 mV accuracy	5	-	-	μs

Table 71. V_{BAT} monitoring characteristics

1. Guaranteed by design.

2. Shortest sampling time can be determined in the application by multiple iterations.

5.3.24 Embedded reference voltage

The parameters given in *Table 72* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{REFINT}	Internal reference voltage	–40 °C < T _A < +105 °C	1.18	1.21	1.24	V
T _{S_vrefint} ⁽¹⁾	ADC sampling time when reading the internal reference voltage	-	10	-	-	μs
V _{RERINT_s} ⁽²⁾	Internal reference voltage spread over the temperature range	V _{DD} = 3 V	-	3	5	mV
T _{Coeff} ⁽²⁾	Temperature coefficient	-	-	30	50	ppm/°C
t _{START} ⁽²⁾	Startup time	-	-	6	10	μs

Table 72. Embedded internal reference voltage

1. Shortest sampling time can be determined in the application by multiple iterations.

2. Guaranteed by design.

Table 73. Internal reference voltage calibration values

Symbol	Parameter	Memory address
V _{REFIN_CAL}	Raw data acquired at temperature of 30 °C, V _{DDA} =3.3 V	0x1FFF 7A2A - 0x1FFF 7A2B

5.3.25 DAC electrical characteristics

Table	74.	DAC	charac	teristics
-------	-----	-----	--------	-----------

Symbol	Parameter	Min	Тур	Мах	Unit	Comments
V _{DDA}	Analog supply voltage	1.8 ⁽¹⁾	-	3.6	V	
V _{REF+}	Reference supply voltage	1.8 ⁽¹⁾	-	3.6	V	V _{REF+} ≤V _{DDA}
V _{SSA}	Ground	0	-	0	V	



PC Card/CompactFlash controller waveforms and timings

Figure 62 through *Figure 67* represent synchronous waveforms, and *Table 83* and *Table 84* provide the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x04;
- COM.FSMC_WaitSetupTime = 0x07;
- COM.FSMC_HoldSetupTime = 0x04;
- COM.FSMC_HiZSetupTime = 0x00;
- ATT.FSMC_SetupTime = 0x04;
- ATT.FSMC_WaitSetupTime = 0x07;
- ATT.FSMC_HoldSetupTime = 0x04;
- ATT.FSMC_HiZSetupTime = 0x00;
- IO.FSMC_SetupTime = 0x04;
- IO.FSMC_WaitSetupTime = 0x07;
- IO.FSMC HoldSetupTime = 0x04;
- IO.FSMC_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 62. PC Card/CompactFlash controller waveforms for common memory read access



1. FSMC_NCE4_2 remains high (inactive during 8-bit access.



Figure 64. PC Card/CompactFlash controller waveforms for attribute memory read access



1. Only data bits 0...7 are read (bits 8...15 are disregarded).





Figure 68. NAND controller waveforms for read access

Figure 69. NAND controller waveforms for write access





6.5 UFBGA176+25 package information



Figure 87. UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline

1. Drawing is not to scale.

Table 95. UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitchball grid array mechanical data

Symbol		millimeters		inches ⁽¹⁾			
Symbol	Min	Тур	Мах	Min	Тур	Мах	
A	-	-	0.600	-	-	0.0236	
A1	-	-	0.110	-	-	0.0043	
A2	-	0.130	-	-	0.0051	-	
A3	-	0.450	-	-	0.0177	-	
A4	-	0.320	-	-	0.0126	-	
b	0.240	0.290	0.340	0.0094	0.0114	0.0134	
D	9.850	10.000	10.150	0.3878	0.3937	0.3996	
D1	-	9.100	-	-	0.3583	-	
E	9.850	10.000	10.150	0.3878	0.3937	0.3996	
E1	-	9.100	-	-	0.3583	-	
е	-	0.650	-	-	0.0256	-	
Z	-	0.450	-	-	0.0177	-	
ddd	-	-	0.080	-	-	0.0031	



Device marking for UFBGA176+25

The following figure gives an example of topside marking and ball A 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.



Figure 89. UFBGA176+25 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



6.6 LQFP176 package information

Figure 90. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package outline



1. Drawing is not to scale.

Table 97. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat packagemechanical data

Symbol		millimeters		inches ⁽¹⁾		
Symbol	Min	Тур	Мах	Min	Тур	Мах
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0571
b	0.170	-	0.270	0.0067	-	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	23.900	-	24.100	0.9409	-	0.9488
HD	25.900	-	26.100	1.0197	-	1.0276

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A.3 Ethernet interface solutions



1. f_{HCLK} must be greater than 25 MHz.

2. Pulse per second when using IEEE1588 PTP optional signal.



Figure 98. RMII with a 50 MHz oscillator

1. f_{HCLK} must be greater than 25 MHz.



Date	Revision	Changes
		Updated Figure 6: Multi-AHB matrix.
		Updated Figure 7: Power supply supervisor interconnection with internal reset OFF
		Changed 1.2 V to V ₁₂ in <i>Section : Regulator OFF</i>
		Updated LQFP176 pin 48.
		Updated Section 1: Introduction.
		Updated Section 2: Description.
		Updated operating voltage in <i>Table 2: STM32F405xx and STM32F407xx: features and peripheral counts.</i>
		Updated Note 1.
		Updated Section 2.2.15: Power supply supervisor.
		Updated Section 2.2.16: Voltage regulator.
		Updated Figure 9: Regulator OFF.
		Updated Table 3: Regulator ON/OFF and internal reset ON/OFF availability.
		Updated Section 2.2.19: Low-power modes.
		Updated Section 2.2.20: VBAT operation.
		Updated Section 2.2.22: Inter-integrated circuit interface (I ² C).
		Updated pin 48 in Figure 15: STM32F40xxx LQFP176 pinout.
		Updated Table 6: Legend/abbreviations used in the pinout table.
		Updated Table 7: STM32F40xxx pin and ball definitions.
		Updated Table 14: General operating conditions.
04-Jun-2013	4 (continued)	Updated Table 15: Limitations depending on the operating power
	(continued)	Supply range.
		Undated Table 34: HSL oscillator characteristics
		Undated Section 5.3.15: 1/O current injection characteristics
		Undated Table 48: I/O static characteristics
		Updated Table 51: NRST pin characteristics
		Updated Table 56: I ² C characteristics.
		Updated Figure 39: I ² C bus AC waveforms and measurement circuit.
		Updated Section 5.3.19: Communications interfaces.
		Updated Table 67: ADC characteristics.
		Added Table 70: Temperature sensor calibration values.
		Added Table 73: Internal reference voltage calibration values.
		Updated Section 5.3.26: FSMC characteristics.
		Updated Section 5.3.28: SD/SDIO MMC card host interface (SDIO) characteristics.
		Updated Table 23: Typical and maximum current consumptions in Stop mode.
		Updated Section : SPI interface characteristics included Table 55.
		Updated Section : I2S interface characteristics included Table 56.
		Updated Table 64: Dynamic characteristics: Eternity MAC signals for SMI.
		Updated Table 66: Dynamic characteristics: Ethernet MAC signals for MII.

Table 100.	Document revision	historv	(continued)
	Document revision	motory	(continued)

